

L Number	Hits	Search Text	DB	Time stamp
1	403	438/197.ccls. and substrate	USPAT	2003/10/31 10:01
2	233	438/197.ccls. and substrate and conductive	USPAT	2003/10/31 10:04
3	138	438/197.ccls. and substrate and conductive and dielectric	USPAT	2003/10/31 10:04
4	371	438/197.ccls. and substrate and conductive and dielectric ahnd "buried drain"	USPAT	2003/10/31 10:05
5	0	438/197.ccls. and substrate and conductive and dielectric and "buried drain"	USPAT	2003/10/31 10:05
6	127	438/197.ccls. and substrate and conductive and dielectric and drain	USPAT	2003/10/31 10:05
7	99	438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4	USPAT	2003/10/31 10:05
8	97	438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4 and silicon	USPAT	2003/10/31 10:05
9	21	438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4 and silicon and cap	USPAT	2003/10/31 10:06
10	19	438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4 and silicon and cap and pattern\$4	USPAT	2003/10/31 10:06
11	19	438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4 and silicon and cap and pattern\$4 and gate	USPAT	2003/10/31 10:06
12	8	438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4 and silicon and cap and pattern\$4 and gate and word	USPAT	2003/10/31 10:06
13	0	438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4 and silicon and cap and pattern\$4 and gate and word and liner	USPAT	2003/10/31 10:06
14	8	438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4 and silicon and cap and pattern\$4 and gate and word and line\$4	USPAT	2003/10/31 10:07
16	1	438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4 and silicon and cap and pattern\$4 and gate and word and line\$4 and metal and salicide	USPAT	2003/10/31 10:19
17	0	438/197.ccls. and substrate and "strip stack"	USPAT	2003/10/31 10:19
18	0	438/197.ccls. and substrate and "strip stacked"	USPAT	2003/10/31 10:19
19	88	438/197.ccls. and substrate and stack	USPAT	2003/10/31 10:20
20	86	438/197.ccls. and substrate and stack and gate	USPAT	2003/10/31 10:20
21	57	438/197.ccls. and substrate and stack and gate and conductive	USPAT	2003/10/31 10:20
22	41	438/197.ccls. and substrate and stack and gate and conductive and dielectric	USPAT	2003/10/31 10:20
23	40	438/197.ccls. and substrate and stack and gate and conductive and dielectric and drain	USPAT	2003/10/31 10:20
24	4	438/197.ccls. and substrate and stack and gate and conductive and dielectric and drain and bit	USPAT	2003/10/31 10:20
25	4	438/197.ccls. and substrate and stack and gate and conductive and dielectric and drain and bit and insulat\$4	USPAT	2003/10/31 10:21

26	4	438/197.ccls. and substrate and stack and gate and conductive and dielectric and drain and bit and insulat\$4 and silicon	USPAT	2003/10/31 10:21
27	3	438/197.ccls. and substrate and stack and gate and conductive and dielectric and drain and bit and insulat\$4 and silicon and cap	USPAT	2003/10/31 10:21
28	3	438/197.ccls. and substrate and stack and gate and conductive and dielectric and drain and bit and insulat\$4 and silicon and cap and pattern\$4	USPAT	2003/10/31 10:21
29	3	438/197.ccls. and substrate and stack and gate and conductive and dielectric and drain and bit and insulat\$4 and silicon and cap and pattern\$4 and word	USPAT	2003/10/31 10:21
30	3	438/197.ccls. and substrate and stack and gate and conductive and dielectric and drain and bit and insulat\$4 and silicon and cap and pattern\$4 and word and line	USPAT	2003/10/31 10:21
31	0	438/197.ccls. and substrate and stack and gate and conductive and dielectric and drain and bit and insulat\$4 and silicon and cap and pattern\$4 and word and line and liner	USPAT	2003/10/31 10:21
32	3	438/197.ccls. and substrate and stack and gate and conductive and dielectric and drain and bit and insulat\$4 and silicon and cap and pattern\$4 and word and line and metal	USPAT	2003/10/31 10:22
33	0	438/197.ccls. and substrate and stack and gate and conductive and dielectric and drain and bit and insulat\$4 and silicon and cap and pattern\$4 and word and line and metal and salicide	USPAT	2003/10/31 10:22
34	3	438/197.ccls. and substrate and stack and gate and conductive and dielectric and drain and bit and insulat\$4 and silicon and cap and pattern\$4 and word and line and metal and silicide	USPAT	2003/10/31 10:22
15	8	438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4 and silicon and cap and pattern\$4 and gate and word and line\$4 and metal	USPAT	2003/10/31 11:08
-	387	438/197.ccls.	USPAT	2003/10/31 10:00
-	378	438/197.ccls. and substrate	USPAT	2003/07/16 11:58
-	89	438/197.ccls. and substrate and "conductive layer"	USPAT	2003/07/16 11:51
-	39	438/197.ccls. and substrate and "conductive layer" and "dielectric layer"	USPAT	2003/07/16 11:51
-	0	438/197.ccls. and substrate and "conductive layer" and "dielectric layer" and "buried drain"	USPAT	2003/07/16 11:51
-	37	438/197.ccls. and substrate and "conductive layer" and "dielectric layer" and "drain"	USPAT	2003/07/16 11:52
-	10	438/197.ccls. and substrate and "conductive layer" and "dielectric layer" and "drain" and "insulating layer"	USPAT	2003/07/16 11:52
-	3	438/197.ccls. and substrate and "conductive layer" and "dielectric layer" and "drain" and "insulating layer" and "silicon layer"	USPAT	2003/07/16 11:53
-	0	438/197.ccls. and substrate and "conductive layer" and "dielectric layer" and "drain" and "insulating layer" and "silicon layer" and cap	USPAT	2003/07/16 11:53

-	2	438/197.ccls. and substrate and "conductive layer" and "dielectric layer" and "drain" and "insulating layer" and "silicon layer" and nitride	USPAT	2003/07/16 11:53
-	2	438/197.ccls. and substrate and "conductive layer" and "dielectric layer" and "drain" and "insulating layer" and "silicon layer" and nitride and gate	USPAT	2003/07/16 11:53
-	6	438/197.ccls. and "non volatile memory"	USPAT	2003/07/16 11:59
-	6	438/197.ccls. and "non volatile memory" and substrate	USPAT	2003/07/16 11:59
-	6	438/197.ccls. and "non volatile memory" and substrate and conductive	USPAT	2003/07/16 12:05
-	2	438/197.ccls. and "non volatile memory" and substrate and conductive and dielectric	USPAT	2003/07/16 12:09
-	0	438/197.ccls. and "strip stack"	USPAT	2003/07/16 12:09
-	83	438/197.ccls. and "stack"	USPAT	2003/07/16 12:09
-	6	438/197.ccls. and "stack structure"	USPAT	2003/07/17 10:42
-	6	438/197.ccls. and "stack structure" and semiconductor	USPAT	2003/07/16 12:10
-	6	438/197.ccls. and "stack structure" and substrate	USPAT	2003/07/16 12:10
-	6	438/197.ccls. and "stack structure" and substrate and gate	USPAT	2003/07/16 12:10
-	4	438/197.ccls. and "stack structure" and substrate and gate and dielectric	USPAT	2003/07/16 12:10
-	0	438/197.ccls. and "stack structure" and substrate and gate and dielectric and buri\$4	USPAT	2003/07/16 12:11
-	4	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain	USPAT	2003/07/16 12:11
-	4	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain and insulat\$4	USPAT	2003/07/16 12:11
-	4	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain and insulat\$4 and silicon	USPAT	2003/07/16 12:11
-	2	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain and insulat\$4 and silicon and cap	USPAT	2003/07/16 12:12
-	1	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain and insulat\$4 and silicon and cap and line\$4	USPAT	2003/07/16 12:12
-	1	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain and insulat\$4 and silicon and cap and line\$4 and salicide	USPAT	2003/07/16 12:13
-	1	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain and insulat\$4 and silicon and cap and line\$4 and salicide and metal	USPAT	2003/07/17 10:42
-	4	438/197.ccls. and "stack structure" and photoresist	USPAT	2003/07/24 11:58
-	1	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain and insulat\$4 and silicon and cap and line\$4 and salicide and metal and photoresist	USPAT	2003/07/17 10:43
-	2	438/197.ccls. and "stack structure" and photoresist and teos	USPAT	2003/07/24 11:58